

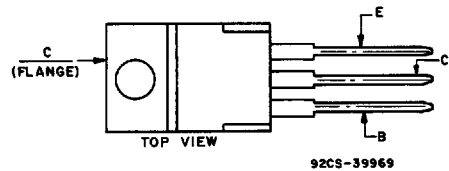
D44C SeriesFile Number **2343**

7-33-05

Silicon N-P-N Transistors**Complementary to the D45C Series****General-Purpose Types for Medium-Power Switching and Amplifier Applications****Features:**

- *Very low collector saturation voltage* [0.5V typ. @ 3.0A I_C]
- *Excellent linearity*
- *Fast switching*

D44C-series n-p-n power transistors are designed for various specific and general purpose applications, such as: output and driver stages of amplifiers operating at frequencies from DC to greater than 1.0 MHz, series, shunt and switching regulators, and low and high frequency inverters/converters.

TERMINAL DESIGNATIONS**JEDEC TO-220AB****MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$) (unless otherwise specified)**

RATING	SYMBOL	D44C1, 2, 3	D44C4, 5, 6	D44C7, 8, 9	D44C10, 11, 12	UNITS
Collector-Emitter Voltage	V_{CEO}	30	45	60	80	Volts
Collector-Emitter Voltage	V_{CES}	40	55	70	90	Volts
Emitter Base Voltage	V_{EBO}	5	5	5	5	Volts
Collector Current — Continuous	I_C	4	4	4	4	A
Peak ⁽¹⁾	I_{CM}	6	6	6	6	
Base Current — Continuous	I_B	2	2	2	2	A
Total Power Dissipation @ $T_A = 25^\circ\text{C}$ @ $T_C = 25^\circ\text{C}$	P_D	1.67 30	1.67 30	1.67 30	1.67 30	Watts
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	-55 to +150	-55 to +150	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	75	75	75	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	4.2	4.2	4.2	4.2	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes: $\frac{1}{8}$ " from Case for 5 Seconds	T_L	+260	+260	+260	+260	$^\circ\text{C}$

(1) Pulse Test Pulse Width = 300ms Duty Cycle $\leq 2\%$.

D44C Series

ELECTRICAL CHARACTERISTICS (T_C = 25°C) (unless otherwise specified)

CHARACTERISTIC	SYMBOL	MIN	TYP	MAX	UNIT
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OFF CHARACTERISTICS⁽¹⁾

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Collector-Emitter Sustaining Voltage (I _C = 100mA)	D44C1, 2, 3 D44C4, 5, 6 D44C7, 8, 9 D44C10, 11, 12	V _{CEO(sus)}	30 45 60 80	— — — —	— — — —	Volts
Collector Cutoff Current (V _{CE} = Rated V _{CE(s)})		I _{CES}	—	—	10	μA
Emitter Cutoff Current (V _{EB} = 5V)		I _{EBO}	—	—	100	μA

SECOND BREAKDOWN

Second Breakdown with Base Forward Biased	FBSOA	SEE FIGURE 3
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ON CHARACTERISTICS⁽¹⁾

DC Current Gain (I _C = 0.2A, V _{CE} = 1V)	D44C1, 4, 7, 10 D44C2, 5, 8, 11 D44C3, 6, 9, 12	h _{FE}	25 100 40	— — —	— 220 120	—
(I _C = 1A, V _{CE} = 1V) (I _C = 2A, V _{CE} = 1V)	D44C1, 4, 7, 10 D44C2, 5, 8, 11 D44C3, 6, 9, 12	h _{FE}	10 20 20	— — —	— — —	—
Collector-Emitter Saturation Voltage (I _C = 1A, I _B = 50mA)	D44C2, 5, 8, 11 D44C3, 6, 9, 12 D44C1, 4, 7, 10	V _{CE(sat)}	— — —	— — —	0.5 0.5 0.5	Volts
(I _C = 1A, I _B = 100mA)						
Base-Emitter Saturation Voltage (I _C = 1A, I _B = 100mA)		V _{BE(sat)}	—	—	1.3	Volts

POWER TRANSISTORS

DYNAMIC CHARACTERISTICS

Collector Capacitance (V _{CB} = 10V, f = 1MHz)	C _{CB0}	—	—	100	pF
Current-Gain — Bandwidth Product (I _C = 20mA, V _{CE} = 4V)	f _T	—	50	—	MHz

SWITCHING CHARACTERISTICS

Resistive Load						
Delay Time + Rise Time	I _C = 1A, I _{B1} = I _{B2} = 0.1A, V _{CC} = 30A, t _p = 25 μsec	t _d + t _r	—	100	—	nS
Storage Time		t _s	—	500	—	
Fall Time		t _f	—	75	—	

(1) Pulse Test PW = 300ms Duty Cycle ≤ 2%.

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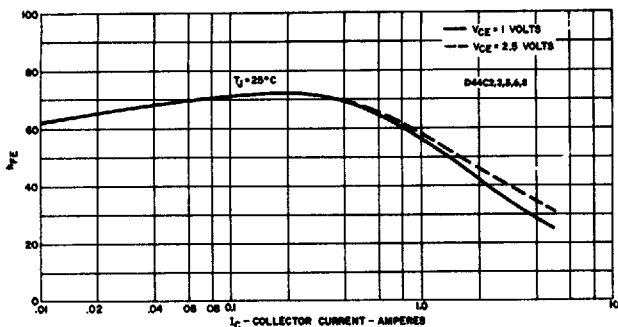


FIG. 1 TYPICAL h_{FE} VS. I_C

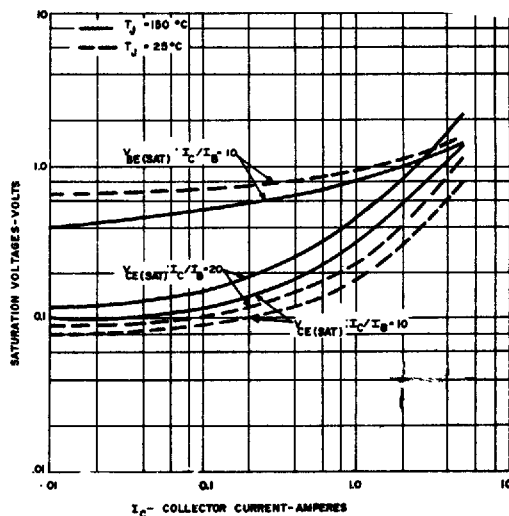


FIG. 2 TYPICAL SATURATION VOLTAGE CHARACTERISTICS

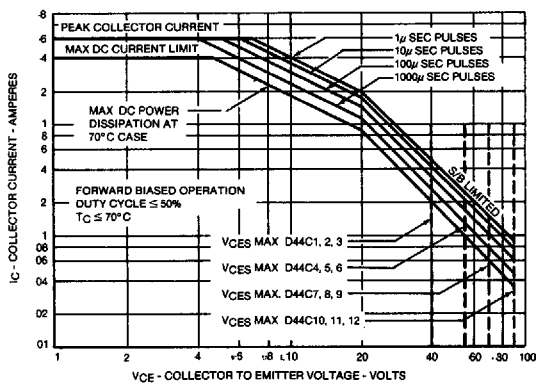


FIG. 3 SAFE REGION OF OPERATION

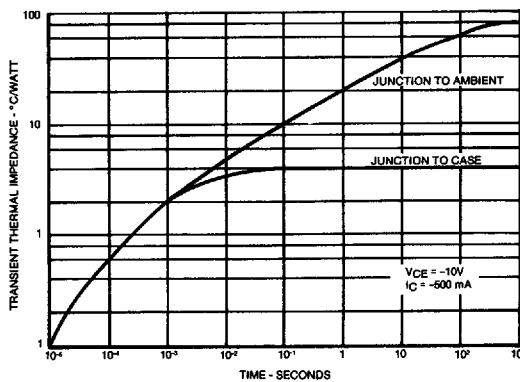


FIG. 4 MAXIMUM TRANSIENT THERMAL IMPEDANCE